

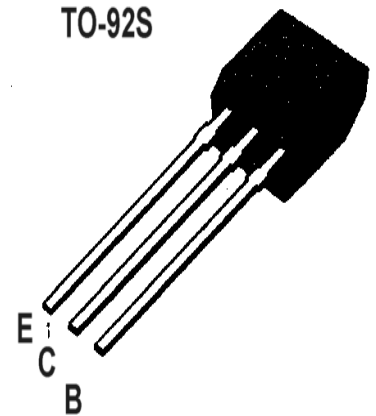
NPN Transistors

—NPN Silicon—

■■ APPLICATION: High Frequency Amplifier Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	40	V
Collector-emitter voltage	V _{CEO}	25	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _c	0.05	A
Collector Power Dissipation	P _c	0.3	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C, R_G=10KΩ)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION		
Collector-Base Breakdown Voltage	BV _{cbo}	40			V	I _c =50uA	I _e =0	
Collector-Emitter Breakdown Voltage	BV _{ceo}	25			V	I _c =1mA	I _b =0	
Emitter-Base Breakdown Voltage	BV _{ebo}	6			V	I _e =50uA	I _c =0	
Collector Cut-off Current	I _{cbo}			0.5	uA	V _{cb} =24V	I _e =0	
Emitter Cut-off Current	I _{ebo}			0.5	uA	V _{eb} =3V	I _c =0	
Collector-Emitter Saturation Voltage	V _{ce(sat)}		0.1	0.3	V	I _c =10mA	I _b =1mA	
DC Current Gain	h _{FE}	82		180	β	V _{ce} =6V	I _c =1mA	
Gain bandwidth product	f _T	150	300		MHz	V _{ce} =6V	I _e =-1mA	f=100MHz
Common Base Output Capacitance	C _{ob}		1	2.2	pF	V _{cb} =6V	I _e =0	f=1MHz

■■ h_{FE} Classification And Marking

Print Mark	C2058S
Classification	P
h _{FE}	82~180

